ABSTRACT

An object of the present invention is to provide a sputtering target for a magnetic recording film, in which a film formation efficiency and film characteristics can be improved by suppressing a growth of crystal grains, by reducing magnetic permeability, and by increasing a density. A method for manufacturing such a sputtering target is also provided. The sputtering target in accordance with the present invention is a sputtering target composed of a matrix phase that includes Co and Pt and a metal oxide phase for instance. The sputtering target for a magnetic recording film has a magnetic permeability in the range of 6 to 15 and a relative density of 90% or more.